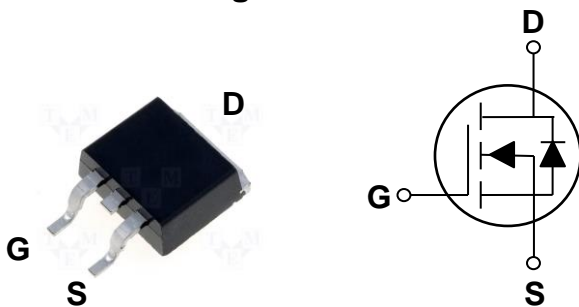


### General Description

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

### TO263 Pin Configuration



BVDSS	R <sub>DS(ON)</sub>	ID
80V	3.9mΩ	120A

### Features

- 80V, 120A, R<sub>DS(ON)</sub> = 3.9mΩ @ V<sub>GS</sub> = 10V
- Improved dv/dt capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available

### Applications

- Networking
- Load Switch
- LED applications
- Quick Charger



### Absolute Maximum Ratings T<sub>c</sub>=25°C unless otherwise noted

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	80	V
V <sub>GS</sub>	Gate-Source Voltage	+20/-12	V
I <sub>D</sub>	Drain Current – Continuous (T <sub>c</sub> =25°C)	120	A
	Drain Current – Continuous (T <sub>c</sub> =100°C)	76	A
I <sub>DM</sub>	Drain Current – Pulsed <sup>1</sup>	480	A
EAS	Single Pulse Avalanche Energy <sup>2</sup>	245	mJ
IAS	Single Pulse Avalanche Current <sup>2</sup>	70	A
P <sub>D</sub>	Power Dissipation (T <sub>c</sub> =25°C)	184	W
	Power Dissipation – Derate above 25°C	1.47	W/°C
T <sub>STG</sub>	Storage Temperature Range	-50 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-50 to 150	°C

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction to ambient	---	62	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction to Case	---	0.68	°C/W

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**
**Off Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	80	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.03	---	V/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =80V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	μA
		V <sub>DS</sub> =64V, V <sub>GS</sub> =0V, T <sub>J</sub> =85°C	---	---	10	μA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =20V, V <sub>DS</sub> =0V	---	---	100	nA

**On Characteristics**

R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	---	3.2	3.9	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A	---	4.6	6.2	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250μA	1	1.6	2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-5.8	---	mV/°C
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =5A	---	10	---	S

**Dynamic and switching Characteristics**

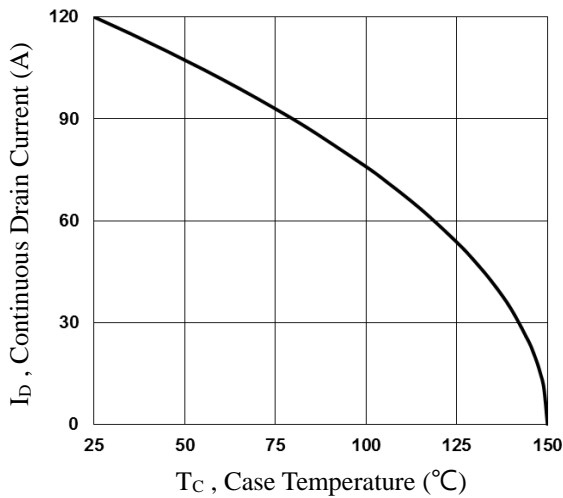
Q <sub>g</sub>	Total Gate Charge <sup>3, 4</sup>	V <sub>DS</sub> =64V, V <sub>GS</sub> =10V, I <sub>D</sub> =10A	---	88	132	nC
Q <sub>gs</sub>	Gate-Source Charge <sup>3, 4</sup>		---	10.2	15	
Q <sub>gd</sub>	Gate-Drain Charge <sup>3, 4</sup>		---	24	32	
T <sub>d(on)</sub>	Turn-On Delay Time <sup>3, 4</sup>	V <sub>DD</sub> =40V, V <sub>GS</sub> =10V, R <sub>G</sub> =6Ω I <sub>D</sub> =1A	---	20	40	ns
T <sub>r</sub>	Rise Time <sup>3, 4</sup>		---	13	26	
T <sub>d(off)</sub>	Turn-Off Delay Time <sup>3, 4</sup>		---	36	72	
T <sub>f</sub>	Fall Time <sup>3, 4</sup>		---	18	36	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, F=1MHz	---	5160	10200	pF
C <sub>oss</sub>	Output Capacitance		---	1346	2700	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	40	80	
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, F=1MHz	---	1.65	---	Ω

**Drain-Source Diode Characteristics and Maximum Ratings**

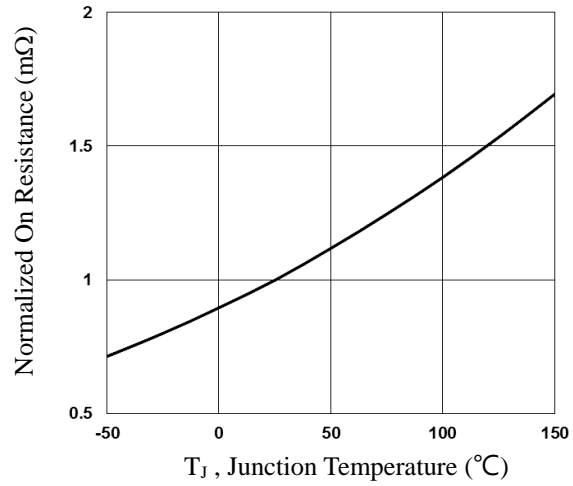
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	120	A
I <sub>SM</sub>	Pulsed Source Current		---	---	240	A
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1	V

Note :

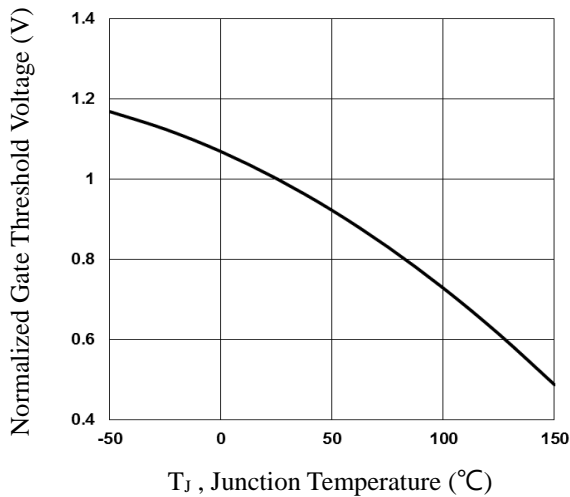
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V<sub>DD</sub>=25V, V<sub>GS</sub>=10V, L=0.1mH, I<sub>AS</sub>=70A., R<sub>G</sub>=25Ω, Starting T<sub>J</sub>=25°C.
3. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
4. Essentially independent of operating temperature.



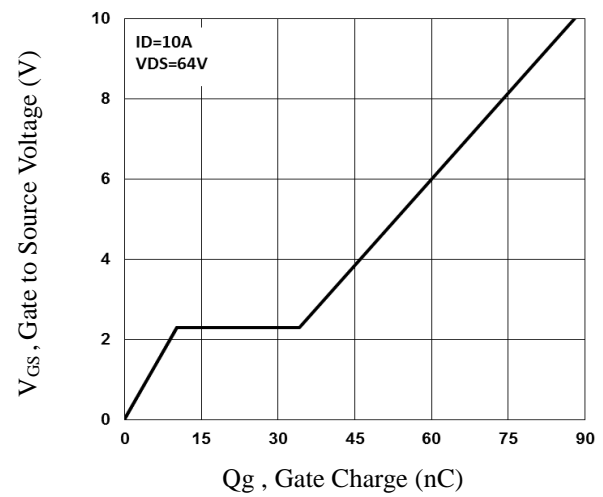
**Fig.1 Continuous Drain Current vs.  $T_C$**



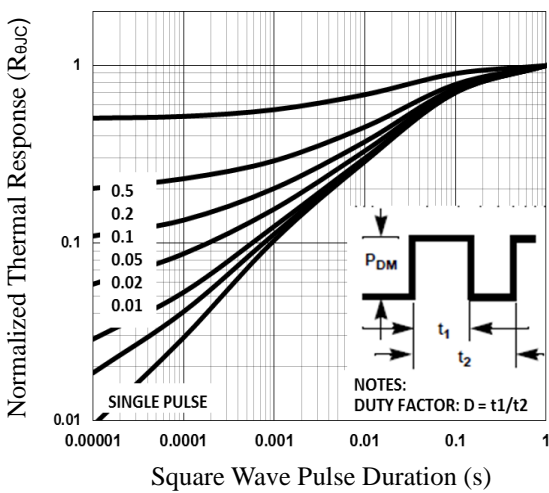
**Fig.2 Normalized  $R_{DS(on)}$  vs.  $T_J$**



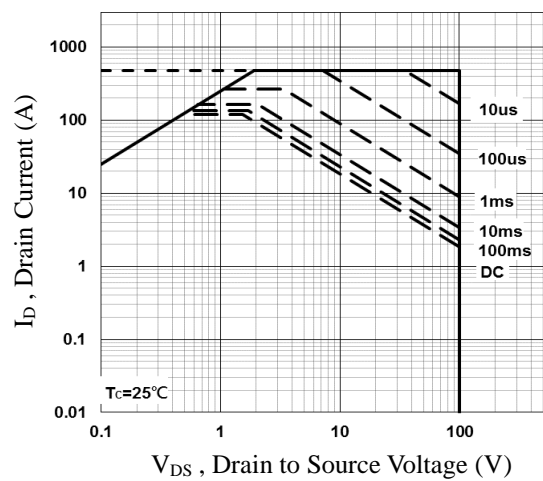
**Fig.3 Normalized  $V_{th}$  vs.  $T_J$**



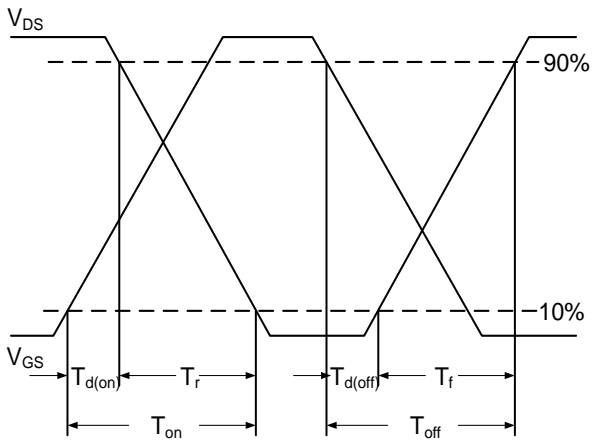
**Fig.4 Gate Charge Characteristics**



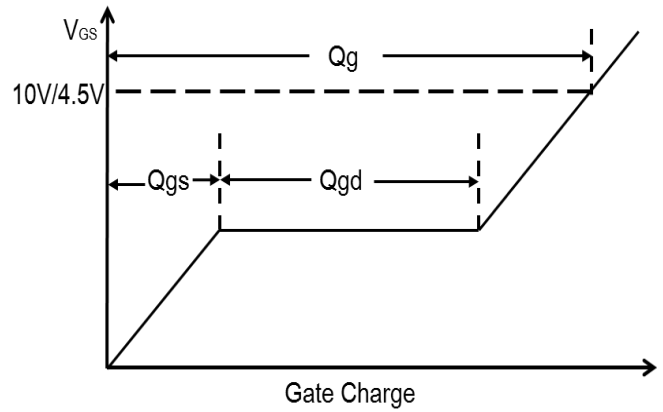
**Fig.5 Normalized Transient Impedance**



**Fig.6 Maximum Safe Operation Area**



**Fig.7 Switching Time Waveform**



**Fig.8 Gate Charge Waveform**

### TO263 PACKAGE INFORMATION

